Preferred Device

Thyristor Surge Protectors

High Voltage Bidirectional TSPD

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover-triggered crowbar protectors. Turn-off occurs when the surge current falls below the holding current value.

Secondary protection applications for electronic telecom equipment at customer premises.

Features

- Outstanding High Surge Current Capability: 100 A 10x1000 μsec Guaranteed at the extended temp range of -20°C to 65°C
- The MMT10B230T3 Series is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68.
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non–Semiconductor Devices
- Fail–Safe, Shorts When Overstressed, Preventing Continued Unprotected Operation
- Surface Mount Technology (SMT)
- Complies with GR1089 Second Level Surge Spec at 500 A 2x10 µsec Waveforms
- 🔊 Indicates UL Registered File #E210057
- Pb–Free Packages are Available



ON Semiconductor®

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BIDIRECTIONAL TSPD (9\) 100 AMP SURGE 265 thru 365 VOLTS





SMB (No Polarity) (Essentially JEDEC DO-214AA) CASE 403C

MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating			Value	Unit
Off-State Voltage – Maximum	MMT10B230T3 MMT10B260T3 MMT10B310T3	V _{DM}	± 170 ± 200 ± 270	V
Maximum Pulse Surge Short Circuit Current Non–Repetitive Double Exponential Decay Waveform (Notes 1 and 2) (–20°C to +65°C) 2 x 10 μsec 10 x 700 μsec 10 x 1000 μsec		Ipps1 Ipps2 Ipps3	± 500 ± 180 ± 100	A(pk)
Maximum Non–Repetitive Rate of Change of On–State Current Double Exponential Waveform, R = 2.0, L = 1.5 μH, C = 1.67 μF, I _{pk} = 110A		di/dt	±100	A/µs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Allow cooling before testing second polarity.

2. Measured under pulse conditions to reduce heating.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T _{J1}	-40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T _{J2}	+175	°C
Instantaneous Peak Power Dissipation (I _{pk} = 100 A, 10x1000 μsec @ 25°C)		4000	W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

ORDERING INFORMATION

Device	Package	Shipping [†]
MMT10B230T3	SMB	
MMT10B230T3G	SMB (Pb–Free)	
MMT10B260T3	SMB	(12mm) Tapo & Pool
MMT10B260T3G	SMB (Pb–Free)	2500 Units per Reel
MMT10B310T3	SMB	
MMT10B310T3G	SMB (Pb–Free)	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

Characteristic		Symbol	Min	Тур	Мах	Unit
Breakover Voltage (Both polarities) (dv/dt = 100 V/μs, I _{SC} = 1.0 A, Vdc = 1000 V) (+65°C)	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G	V _(BO)	- - -	- - -	265 320 365	V
	MMT10B23013, G MMT10B260T3, G MMT10B310T3, G		-	- - -	290 340 400	
Breakover Voltage (Both polarities) (f = 60 Hz, I_{SC} = 1.0 A(rms), V_{OC} = 1000 V(rms), R ₁ = 1.0 kΩ, t = 0.5 cycle) (Note 3) (+65°C)	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G	V _(BO)			265 320 365 290 340 400	V
Breakover Voltage Temperature Coefficient		dV _(BO) /dT _J	_	0.08	_	%/°C
Breakdown Voltage (I _(BR) = 1.0 mA) Both polarities	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G	V _(BR)		190 240 280	- - -	V
Off State Current (V_{D1} = 50 V) Both polarities (V_{D2} = V_{DM}) Both polarities		I _{D1} I _{D2}		-	2.0 5.0	μΑ
On–State Voltage (I _T = 1.0 A) (PW \leq 300 µs, Duty Cycle \leq 2%) (Note 3)		V _T	-	1.53	5.0	V
Breakover Current (f = 60 Hz, V _{DM} = 1000 V(rms), Both polarities	R _S = 1.0 kΩ)	I _{BO}	-	260	-	mA
Holding Current (Both polarities) $V_S = 500$ Volts; I _T (Initiating Current) = ± 1.0 A	(Note 3)	Iн	150	270	-	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V_D = Rated V_{BR} , T_J = 25°C)		dv/dt	2000	-	-	V/µs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signa (f = 1.0 MHz, 2.0 Vdc, 15 mV rms Sign	nal)	C _O		65 160	_ 200	pF

3. Measured under pulse conditions to reduce heating.

Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter		
I _{D1} , I _{D2}	Off State Leakage Current		
V _{D1} , V _{D2}	Off State Blocking Voltage		
V_{BR}	Breakdown Voltage		
V _{BO}	Breakover Voltage		
I _{BO}	Breakover Current		
I _H	Holding Current		
V _{TM}	On State Voltage		





Figure 1. Off-State Current versus Temperature

Figure 2. Breakdown Voltage versus Temperature



Figure 3. Breakover Voltage versus Temperature



Figure 5. Exponential Decay Pulse Waveform

Figure 4. Holding Current versus Temperature



Figure 6. Peak Surge On–State Current versus Surge Current Duration, Sinusoidal Waveform



*Polymeric PTC (positive temperature coefficient) overcurrent protection device



PACKAGE DIMENSIONS

SMB (No Polarity) (Essentially JEDEC DO–214AA) CASE 403C–01 ISSUE A





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982

Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.180	4.06	4.57
В	0.130	0.150	3.30	3.81
С	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
Н	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
Р	0.020	REF	0.51	REF
S	0.205	0.220	5.21	5.59

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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